

Title (en)

Method of manufacturing cold cathode field emission device and method of manufacturing cold cathode field emission display

Title (de)

Verfahren zur Herstellung eines Kaltkathodenfeldemitters und einer Anzeigevorrichtung

Title (fr)

Procédé de fabrication d'un émetteur de champ à cathode froide et d'un dispositif d'affichage

Publication

EP 1073085 A3 20030409 (EN)

Application

EP 00402144 A 20000727

Priority

JP 21547999 A 19990729

Abstract (en)

[origin: EP1073085A2] A method of manufacturing a cold cathode field emission device, which comprises the steps of; (A) forming a cathode electrode (11) on a support (10), (B) forming an insulating layer (12) on the cathode electrode (11) and the support (10), (C) forming a gate electrode (13A) on the insulating layer (12), (D) forming an opening portion (14) having a bottom portion where the cathode electrode (11) is exposed, at least in the insulating layer (12), (E) forming an electron emitting electrode composed of an electric conductive composite (17) containing electric conductive particles and a binder on the cathode electrode (11) exposed in the bottom portion of the opening portion (14), and (F) removing the binder in a surface layer portion of the electron emitting electrode to expose the electric conductive particles on the surface of the electron emitting electrode (17A). <IMAGE>

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CPC (source: EP)

H01J 9/025 (2013.01)

Citation (search report)

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